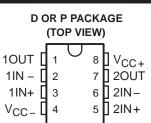
LF412C DUAL JFET-INPUT OPERATIONAL AMPLIFIER

SLOS010B - MARCH 1987 - REVISED AUGUST 1994

- Low Input Bias Current . . . 50 pA Typ
- Low Input Noise Current 0.01 pA/√Hz Typ
- Low Supply Current . . . 4.5 mA Typ
- High Input impedance . . . $10^{12} \Omega$ Typ
- Internally Trimmed Offset Voltage
- Wide Gain Bandwidth . . . 3 MHz Typ
- High Slew Rate ... 13 V/µs Typ

description

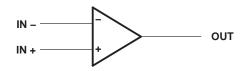


This device is a low-cost, high-speed, JFET-input operational amplifier with very low input offset voltage and a specified maximum input offset voltage drift. It requires low supply current yet maintains a large gain bandwidth product and a fast slew rate. In addition, the matched high-voltage JFET input provides very low input bias and offset currents.

The LF412C can be used in applications such as high-speed integrators, digital-to-analog converters, sample-and-hold circuits, and many other circuits.

The LF412C is characterized for operation from 0°C to 70°C.

symbol (each amplifier)



AVAILABLE OPTIONS

	Viemov	PACKAG	ε
Τ _Α	V _{IO} max AT 25°C	SMALL OUTLINE (D)	PLASTIC DIP (P)
0°C to 70°C	3 mV	LF412CD	LF412CP

The D packages are available taped and reeled. Add the suffix R to the device type (ie., LF412CDR).

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{CC+} Supply voltage, V _{CC-}	
Differential input voltage, VID	
Input voltage, V _I (see Note 1)	±15 V
Duration of output short circuit	unlimited
Continuous total power dissipation	
Operating temperature range	0°C to 70°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

NOTE 1: Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.



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recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V _{CC +}	3.5	18	V
Supply voltage, V _{CC –}	-3.5	-18	V

electrical characteristics over operating free-air temperature range, $V_{CC\pm} = \pm 15$ V (unless otherwise specified)

	PARAMETER	TEST C	ONDITIONS	T _A †	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_{IC} = 0,$	$R_S = 10 \text{ k}\Omega$	25°C		1	3	mV
αVIO	Average temperature coefficient of input offset voltage	$V_{IC} = 0,$	R _S = 10 kΩ			10	20‡	μV/°C
	land affect annual S			25°C		25	100	pА
IIO	Input offset current§	$\Lambda^{IC} = 0$		70°C			4	nA
	3	V 0		25°C		50	200	pА
IIB	Input bias current§	$V_{IC} = 0$		70°C			8	nA
VICR	Common-mode input voltage range				±11	– 11.5 to 14.5		V
VOM	Maximum peak output voltage swing	$R_L = 10 \ k\Omega$			±12	±13.5		V
				25°C	25	200		
AVD	Large-signal differential voltage	$V_{O} = \pm 10 V,$	$R_L = 2 k\Omega$	Full range	15	200		V/mV
ri	Input resistance	T _A = 25°C				1012		Ω
CMRR	Common-mode rejection ratio	$R_S \le 10 \ k\Omega$			70	100		dB
k SVR	Supply-voltage rejection ratio	See Note 2			70	100		dB
ICC	Supply current					4.5	6.8	mA

[†] Full range is 0°C to 70°C.

[‡] At least 90% of the devices meet this limit for α_{VIO} .

§ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperatures as close to the ambient temperature as possible.

NOTE 2: Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

operating characteristics, V_{CC\pm} = ±15 V, T_A = 25°C

	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
V ₀₁ /V ₀₂	Crosstalk attenuation	f = 1 kHz			120		dB
SR	Slew rate			8	13		V/µs
B ₁	Unity-gain bandwidth			2.7	3		MHz
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		18		nV/√Hz
۱ _n	Equivalent input noise current	f = 1 kHz			0.01		pA/√Hz





PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	•		Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material (6)	(3)		(4/5)	
LF412 MWC	ACTIVE	WAFERSALE	YS	0	1	RoHS & Green	Call TI	Level-1-NA-UNLIM	-40 to 85		Samples
LF412CD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF412C	
LF412CDE4	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF412C	
LF412CDG4	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF412C	
LF412CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF412C	Samples
LF412CDRE4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70		Samples
LF412CDRG4	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	0 to 70		Samples
LF412CP	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	LF412CP	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



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PACKAGE OPTION ADDENDUM

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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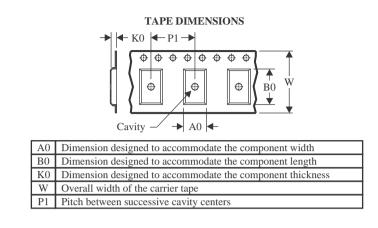
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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*A	l dimensions are nominal												
	Device	•	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	LF412CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
	LF412CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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PACKAGE MATERIALS INFORMATION

10-Jan-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LF412CDR	SOIC	D	8	2500	356.0	356.0	35.0
LF412CDR	SOIC	D	8	2500	340.5	338.1	20.6

TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LF412CD	D	SOIC	8	75	507	8	3940	4.32
LF412CDE4	D	SOIC	8	75	507	8	3940	4.32
LF412CDG4	D	SOIC	8	75	507	8	3940	4.32
LF412CP	Р	PDIP	8	50	506	13.97	11230	4.32

D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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